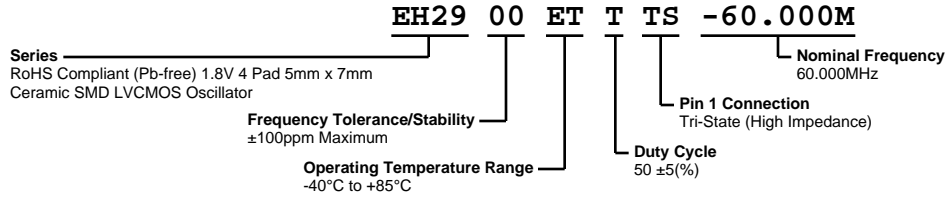


EH2900ETTS-60.000M



ELECTRICAL SPECIFICATIONS

| | |
|---------------------------------------|---|
| Nominal Frequency | 60.000MHz |
| Frequency Tolerance/Stability | ± 100 ppm Maximum (Inclusive of all conditions: Calibration Tolerance at 25°C , Frequency Stability over the Operating Temperature Range, Supply Voltage Change, Output Load Change, First Year Aging at 25° , 260°C Reflow, Shock, and Vibration) |
| Aging at 25°C | ± 5 ppm/Year Maximum |
| Operating Temperature Range | -40°C to $+85^{\circ}\text{C}$ |
| Supply Voltage | 1.8Vdc $\pm 5\%$ |
| Input Current | 4mA Maximum (No Load) |
| Output Voltage Logic High (Voh) | 90% of Vdd Minimum (IOH = -8mA) |
| Output Voltage Logic Low (Vol) | 10% of Vdd Maximum (IOL = +8mA) |
| Rise/Fall Time | 4nSec Maximum (Measured at 20% to 80% of waveform) |
| Duty Cycle | $50 \pm 5(\%)$ (Measured at 50% of waveform) |
| Load Drive Capability | 15pF Maximum |
| Output Logic Type | CMOS |
| Pin 1 Connection | Tri-State (High Impedance) |
| Tri-State Input Voltage (Vih and Vil) | 90% of Vdd Minimum or No Connect to Enable Output, 10% of Vdd Maximum to Disable Output (High Impedance) |
| Standby Current | 10 μ A Maximum (Pin 1 = Ground) |
| Absolute Clock Jitter | ± 100 pSec Maximum |
| Start Up Time | 10mSec Maximum |
| Storage Temperature Range | -55°C to $+125^{\circ}\text{C}$ |

ENVIRONMENTAL & MECHANICAL SPECIFICATIONS

| | |
|------------------------------|---|
| ESD Susceptibility | MIL-STD-883, Method 3015, Class 1, HBM: 1500V |
| Fine Leak Test | MIL-STD-883, Method 1014, Condition A |
| Flammability | UL94-V0 |
| Gross Leak Test | MIL-STD-883, Method 1014, Condition C |
| Mechanical Shock | MIL-STD-883, Method 2002, Condition B |
| Moisture Resistance | MIL-STD-883, Method 1004 |
| Moisture Sensitivity | J-STD-020, MSL 1 |
| Resistance to Soldering Heat | MIL-STD-202, Method 210, Condition K |
| Resistance to Solvents | MIL-STD-202, Method 215 |
| Solderability | MIL-STD-883, Method 2003 |
| Temperature Cycling | MIL-STD-883, Method 1010, Condition B |
| Vibration | MIL-STD-883, Method 2007, Condition A |

EH2900ETTTS-60.000M

MECHANICAL DIMENSIONS (all dimensions in millimeters)



| PIN | CONNECTION |
|-----|----------------|
| 1 | Tri-State |
| 2 | Case Ground |
| 3 | Output |
| 4 | Supply Voltage |

| LINE | MARKING |
|------|---|
| 1 | ECLIPTEK |
| 2 | 60.000M |
| 3 | XXXXXX XXXXXX=Ecliptek Manufacturing Identifier |

Suggested Solder Pad Layout

All Dimensions in Millimeters



All Tolerances are ±0.1

EH2900ETTTS-60.000M

OUTPUT WAVEFORM & TIMING DIAGRAM



Test Circuit for CMOS Output



Note 1: An external 0.01 μ F ceramic bypass capacitor in parallel with a 0.1 μ F high frequency ceramic bypass capacitor close (less than 2mm) to the package ground and supply voltage pin is required.

Note 2: A low capacitance (<12pF), 10X attenuation factor, high impedance (>10Mohms), and high bandwidth (>300MHz) passive probe is recommended.

Note 3: Capacitance value C_L includes sum of all probe and fixture capacitance.

Recommended Solder Reflow Methods



High Temperature Infrared/Convection

| | |
|--|---|
| $T_s \text{ MAX}$ to T_L (Ramp-up Rate) | 3°C/second Maximum |
| Preheat | |
| - Temperature Minimum ($T_s \text{ MIN}$) | 150°C |
| - Temperature Typical ($T_s \text{ TYP}$) | 175°C |
| - Temperature Maximum ($T_s \text{ MAX}$) | 200°C |
| - Time ($t_s \text{ MIN}$) | 60 - 180 Seconds |
| Ramp-up Rate (T_L to T_p) | 3°C/second Maximum |
| Time Maintained Above: | |
| - Temperature (T_L) | 217°C |
| - Time (t_L) | 60 - 150 Seconds |
| Peak Temperature (T_p) | 260°C Maximum for 10 Seconds Maximum |
| Target Peak Temperature ($T_p \text{ Target}$) | 250°C +0/-5°C |
| Time within 5°C of actual peak (t_p) | 20 - 40 seconds |
| Ramp-down Rate | 6°C/second Maximum |
| Time 25°C to Peak Temperature (t) | 8 minutes Maximum |
| Moisture Sensitivity Level | Level 1 |
| Additional Notes | Temperatures shown are applied to body of device. |

Recommended Solder Reflow Methods



Low Temperature Infrared/Convection 240°C

| | |
|--|--|
| T_s MAX to T_L (Ramp-up Rate) | 5°C/second Maximum |
| Preheat | |
| - Temperature Minimum (T _s MIN) | N/A |
| - Temperature Typical (T _s TYP) | 150°C |
| - Temperature Maximum (T _s MAX) | N/A |
| - Time (t _s MIN) | 60 - 120 Seconds |
| Ramp-up Rate (T_L to T_p) | 5°C/second Maximum |
| Time Maintained Above: | |
| - Temperature (T _L) | 150°C |
| - Time (t _L) | 200 Seconds Maximum |
| Peak Temperature (T_p) | 240°C Maximum |
| Target Peak Temperature (T_p Target) | 240°C Maximum 1 Time / 230°C Maximum 2 Times |
| Time within 5°C of actual peak (t_p) | 10 seconds Maximum 2 Times / 80 seconds Maximum 1 Time |
| Ramp-down Rate | 5°C/second Maximum |
| Time 25°C to Peak Temperature (t) | N/A |
| Moisture Sensitivity Level | Level 1 |
| Additional Notes | Temperatures shown are applied to body of device. |

Low Temperature Manual Soldering

185°C Maximum for 10 seconds Maximum, 2 times Maximum. (Temperatures shown are applied to body of device.)

High Temperature Manual Soldering

260°C Maximum for 5 seconds Maximum, 2 times Maximum. (Temperatures shown are applied to body of device.)